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Date: January 7, 2004

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Message:			
In re Application of			
Stephen E. Savas Application No.: 10/053,138 Filed: 01/18/2002	Group Art Unit: 17 Examiner: Parviz	Hassanzadeh	
For: Pulsed Plasma Processing of \$	Semiconductor Sub	strates	
Please see attached Transmittal, Fe referenced matter.	e Transmittal, and	Response to Office	Action in the above-

Ref: 14912.786

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PTO/SB/21 (08-03) Approved for use through 07/31/2006, OMB 0851-0031 U.S. Petent and Trademerk Office; U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number. Application Number 10/053,138 TRANSMITTAL January 18, 2002 Filing Date **FORM** Stephen E. Savas First Named Inventor (to be used for all correspondence after initial filling) 1763 Parviz Hassanzadeh Examiner Total Number of Pages In This Submission Attorney Docket Number 14912.786 **ENCLOSURES** (Check all that apply) 冈 Fee Transmittal Form Drawing(e) After Allowance Communication to Group Fee Attached Licensing-related Papers Appeal Communication to Board of Appeals and Interferences Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Amendment/Reply Petition Petition to Convert to a Provisional Application After Final Proprietary Information Affidavlts/declaration(s) Power of Attorney, Revocation Change of Correspondence Address Status Letter Extension of Time Request Terminal Discialmer Other Englosure(s) (please Express Abandonment Request Request for Refund Information Disclosure Statement CD, Number of CD(s) Remarks Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53 SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT Firm Michael J. Murphy, Reg. No. 37,404; Customer No. 21971 Individual Signature Date January 7, 2004 CERTIFICATE OF TRANSMISSION/MAILING I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the United States Postal Service with sufficient postage as first class mall in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the date shown below.

This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will very depending upon the Individual case. Any comments on the amount of time you require to complete this form and/or auggestions for reducing this burden, should be sent to the Chief information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS, SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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January 7, 2004

Date

Michael J. Murphy (via facsimile 703-872-9306)

P. 3

PTO/SB/17 (6/99)

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FEE TRANSMITTAL			Complete if Known									
for FY 2004						Application Number 10/053,138 Filing Datz Jan. 18, 2002						
Patent fees are subject to annual revision.									Jan. 18, 2002			
Small Entity payments must be supported by a small entity statement,					lamed inv		-	Stephen E. Savas				
otherwise large entity fees must be pald. See Forms PTO/SB/09-12.  See 37 C.F.R. §§ 1.27 and 1.28.					_		Parviz Hassanzadch					
TOTAL AMOUN	T OF PA	YMENT	(S) 950		<del></del>	Group/Art Unit 1763						
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SUBMITTED BY									Complete (if applicable)			
Name (Print/Type)	Michael J	. Murphy			Registrati		37,404		Telephone 650-493-	9300		
Signature Date January 7, 20					, 2004		Customer No. 02197	1				
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Attorney Docket No. 14912,786

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE						CENTRAL FAX CENTER		
In re Application of		) .				JAN 0 7 2004		
Stephen E. Savas		) Gro	Group Art Unit: 1763			ALLA		
Applic	eation No.: 10/053,138	) Exa	miner:	Parviz Hassanz	adeh			
Filed:	01/18/2002	)						
For:	Pulsed Plasma Processing of Semiconductor Substrates	·) )						

## Response to Office Action

Mail Stop: Amendment Commissioner for Patents PO Box 1450 Alexandria VA 22313-1450

Sir:

In an office action dated July 7, 2003, the Examiner rejected pending claims 44-82. The Examiner rejected claims 44-56 and 60-63 under 103(a) as being unpatentable over U.S. Patent 5,289,010 ("Shohet") in view of WO 91/10341 ("Savas") and rejected claims 57-59 and 64-82 under 103(a) as being unpatentable over Shohet in view of Savas and further in view of U.S. Patent 4,858, 516 ("Corn"). In this response, applicant respectfully traverses the Examiner's rejection of pending claims 44-82.

Claims 44 and 64 are independent claims and claims 45-63 and claims 65-82 depend from those claims, respectively.

Claim 44 is directed at a method of plasma processing a semiconductor substrate comprising, among other things, inductively coupling power to a plasma using high power cycles and low power cycles such that greater than about 5kW of power is coupled to the plasma during each high power cycle; coupling power to a substrate support using high power cycles and low power cycles; and

synchronizing such that the high power cycles are applied to the substrate support substantially during the time that low power cycles are applied to the plasma.

Claim 64 is directed at a method of plasma processing a semiconductor substrate comprising, among other things, inductively coupling power to a plasma using high power cycles and low power cycles with a duty cycle of about 5 to 30 percent; coupling power to a substrate support using high power cycles and low power cycles; and synchronizing such that the high power cycles are applied to the substrate support substantially during the time that low power cycles are applied to the plasma.

In rejecting independent claims 44 and 64, the Examiner relies upon Shohet as teaching a plasma power source 36 modulated by a pulse modulator 38 such that "whereas as shown in Fig. 3, plasma excitation is on except during the time a pulsed voltage is applied to the substrate support".

Shohet describes a plasma source ion implantation process and apparatus. A plasma may be created by ionizing a neutral gas. However, unwanted species may also be ionized when generating the plasma. See col. 1, lines 65-67 and col. 2, lines 9-10 and 17-21. Shohet teaches the use of ion cyclotron resonance (ICR) in the presence of a magnetic field to purify the ions and drive unwanted ion species into resonance and into a collection plate or other collection means. See col. 2, lines 21-30. The frequency, magnetic field, electric field and other parameters are selected in relation to one another to achieve the desired resonance and resulting purification. See col. 4, lines 6-68 and col. 5, lines 1-24. In Figures 1 and 2 of Shohet, a magnet 22 provides a magnetic field between plate-like electrodes 17 and plates 19 to form the ICR system. This ICR system is separate from the plasma source 16 and plasma source power supply 36 used to ionize the gas.

Figure 3 in Shohet, referenced by the Examiner, illustrates acceleration pulses 61 applied to the target and the ICR excitation 64 and 69 which are applied to the excitation electrodes 17. See col. 7, lines 39-51. The ICR excitation signals 64 and 69 in Figure 3 are the signals used to purify ions after the plasma is generated and are not signals used to generate the plasma. See also col. 6, lines 14-20

(the plasma source 16 creates the plasma which drifts into the ion purification region and "Once the ions are in the ion purification region, the time varying electric field from the excitation electrode 17 serves to sweep out the undesired species").

While the ICR in Shohet applies an excitation signal to the plasma, it uses a magnet and platelike electrodes (and the corresponding excitation signals in Figure 3 of Shohet) and does not teach or
suggest inductively coupling power into the plasma in the manner set forth in independent claims 44
and 64 of the present application. Moreover, there is no suggestion to substitute the plasma source or
power signals in Savas for the ICR purification in Shohet. Shohet teaches that the frequency, magnetic
field, electric field and other parameters are selected in relation to one another to achieve the desired
resonance. There is no teaching or suggestion to combine the higher power levels of Savas cited by the
Examiner to the ion purification excitation signals in Figure 3 of Shohet. In addition, the plasma
source in Savas does not purify ions for ion implantation as desired in Shohet and substituting it for the
ICR in Shohet would render Shohet inoperable for its intended purpose. In addition, substituting the
plasma source in Savas for the plasma source in Shohet also would not result in the claimed invention,
because the excitation signals shown in Figure 3 do not apply to the power source (and, in any event,
the plasma source of Savas does not use high and low power cycles of the type required by
independent claims 44 and 64).

Corn also does not make up for the deficiencies in Shohet. Corn describes parallel plate electrodes which would capacitively (rather than inductively) couple power into a plasma. High and low frequency signals are applied to the electrodes for an etch process. Corn does not teach or suggest inductively coupling power into a reactor in the manner set forth in independent claims 44 and 64. In addition, there is no suggestion to combine the duty cycles used for the etch process in Corn with the ion implantation reactor described in Shohet. The ion implantation reactor uses high voltage

acceleration pulses to implant ions and does not use dual RF frequency signals of the type used for etching in Corn.

Methods using inductively coupled plasmas in accordance with the claimed invention can be used to provide important advantages by reducing charge build up and microsteering, a problem not recognized or addressed by the above references.

In view of the above, applicant believes that independent claims 44 and 64 are not anticipated or rendered obvious by Shohet either alone or in view of Savas and Corn. Therefore, claims 44 and 64 are believed to be patentable. Claims 45-63 and claims 65-82 depend from independent claims 44 and 64 and, as a result, are also believed to be patentable.

In view of the foregoing, it is believed that all of the pending claims are in condition for allowance. Applicant respectfully requests reconsideration, allowance and passage to issue of the claims as amended.

The Commissioner is authorized to charge any additional fees which may be required, including petition fees, or credit any overpayment to Deposit Account No. 23-2415 (Docket No. 14912-786).

Respectfully submitted,

WILSON SONSINI GOODRICH & ROSATI

Date: January 7, 2004

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